

## UPCOMING CONFERENCES

### Second "Nano and Giga Challenges in Microelectronics" Conference Set for September 2004 in Cracow

Microelectronics technologies have reached the stage in their development where the ultimate miniaturization of electronic devices is approaching atomic dimensions, the interconnect bottleneck is posing a limit to circuit speeds, new materials are being introduced into microelectronic manufacturing at an unprecedented rate, and alternative technologies to mainstream complementary metal oxide semiconductors (CMOSs) are being considered. As a combination of today's microelectronics, tomorrow's nanoelectronics, and the future's molecular electronics, a series of conferences on Nano and Giga Challenges in Microelectronics (NGCM) is being launched. Following the inaugural summer school and symposium held in Moscow in 2002 (NGCM2002), the second biennial meeting will be held in Cracow, Poland, September 13–17, 2004, hosted by Jagiellonian University.

The meeting opens with a two-day summer school, followed by the three-day symposium. The summer school provides an overview of the current status of the field and offers plenary tutorial lectures and panel discussions involving speakers and attendees. The symposium includes plenary talks in the mornings, followed by oral and poster presentations in the afternoons. Evening sessions will focus on technology trends and opportunities for collaboration.

Academic and industrial researchers are invited to present tutorial, expository, and original research papers dedicated to scientific and advanced technology problems related to the ultimate merge of micro- and nanoelectronics in the following areas:

- Atomic-scale design: theory and experiment;
- Bio- and molecular electronics;
- Highest-frequency electronics;
- Fabrication of nanodevices;
- Magnetic materials and spintronics;
- Materials and processes for integrated and subwave optoelectronics;
- New materials for gate and dielectrics in field-effect transistors;
- Nonsilicon materials and devices;
- Quantum effects in devices; and
- System design technologies.

**The deadline for abstract submission is April 15, 2004.** On-line registration, abstract submission, and updated information, including frequently asked questions (FAQs), are available on the meeting Web site at <http://asdn.net/ngcm2004>.

Alternatively, for more information on the meeting program or general information, contact the program committee chair,

Anatoli Korkin, at Nano and Giga Solutions Inc., 1683 E. Spur St., Gilbert, AZ 85296 USA; tel./fax 480-539-4754 and e-mail [korkin@nanoandgiga.com](mailto:korkin@nanoandgiga.com). For more information on registration, contact Jan K. Labanowski, Science Computing Facility, 225 Nieuwland Science Hall, University of Notre Dame, Notre Dame, IN 46556 USA; e-mail [jkl@asdn.net](mailto:jkl@asdn.net). For more information on accommodations, contact Jadwiga Rudzinska in Cracow at e-mail [jadwiga@makolab.pl](mailto:jadwiga@makolab.pl). □

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For more information about the Hall Effect Measurement System, contact Bob Paugh at 650 / 962-9620 or [bobp@mmr.com](mailto:bobp@mmr.com). Or visit our web page at <http://www.mmr.com>.

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